16 August 2024

Product data sheet

1. General description

General purpose MOSFET for standard applications, 180 A, standard level N-channel enhancement mode Power MOSFET in MLPAK56 package.

2. Features and benefits

- Standard level compatibility
- Trench MOSFET technology
- Thermally efficient package in a small form factor (5.15 mm x 6.15 mm footprint)

3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Home appliance
- · Motor drive
- · Load switching
- · LED lighting
- E-bike

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	180	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	181	W
Tj	junction temperature			-55	-	150	°C
Static chara	acteristics			'		'	
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$		-	2.65	2.9	mΩ
Dynamic ch	naracteristics					'	
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V;		-	19	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>		-	74	-	nC
Avalanche	ruggedness			,			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 52.5 A; $V_{sup} \le 100 \text{ V}$; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[1]	-	-	275.6	mJ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain o	liode						
Q _r	recovered charge	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 50 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 15	[2]	-	48	-	nC

^[1] Protected by 100% test

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source		
3	S	source]	D 1
4	G	gate		
5	D	drain		G—(F)
6	D	drain		mbb076 S
7	D	drain	8 7 6 5	
8	D	drain	MLPAK56 (SOT8038-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PXN2R9-100RS	MLPAK56	plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 1.27 mm; 6 x 5 x 1.0 mm body	SOT8038-1		

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN2R9-100RS	2R9-100

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C	-	100	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	181	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	180	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	114	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3	-	722	Α
T _{stg}	storage temperature		-55	150	°C

^[2] includes capacitive recovery

Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	150	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode			'	•	
Is	source current	T _{mb} = 25 °C		-	151	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	722	Α
Avalanche r	uggedness			'	,	'
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 52.5 A; $V_{sup} \le 100$ V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	[1]	-	275.6	mJ
I _{AS}	non-repetitive avalanche current	$T_{j(init)} = 25 ^{\circ}C$	[1]	-	52.5	А

[1] Protected by 100% test

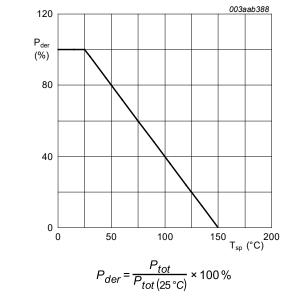


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

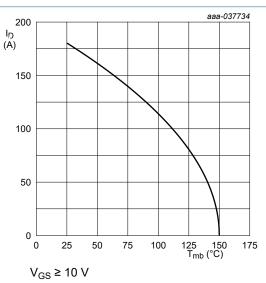


Fig. 2. Continuous drain current as a function of mounting base temperature

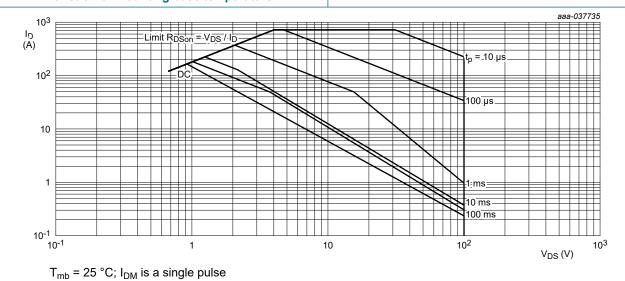


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

N-channel 100 V, 2.9 mOhm, standard level Trench MOSFET in MLPAK56

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.57	0.69	K/W



10. Characteristics

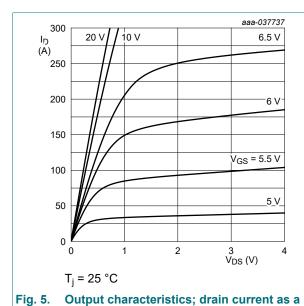
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics		'	'		'
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	-	100	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 0.25 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C};$ Fig. 8	2.5	3	4	V
		I _D = 0.25 mA; V _{DS} =V _{GS} ; T _j = 150 °C	-	1.6	-	V
		$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	3.7	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-11.2	-	mV/K
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.07	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 150 °C	-	74	-	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$	-	2.65	2.9	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 10	-	-	5.6	mΩ
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.7	-	Ω

N-channel 100 V, 2.9 mOhm, standard level Trench MOSFET in MLPAK56

Symbol	Parameter	Conditions	М	in Typ	Max	Unit
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	74	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$	-	62	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V;	-	22	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 11; Fig. 12</u>	-	13	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	9	-	nC
Q _{GD}	gate-drain charge		-	19	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 50 V; T _j = 25 °C; Fig. 11; Fig. 12	-	4.9	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 13$	-	4892	-	pF
C _{oss}	output capacitance		-	1948	-	pF
C _{rss}	reverse transfer capacitance		-	29	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$	-	21	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	27	-	ns
t _{d(off)}	turn-off delay time		-	46	-	ns
t _f	fall time		-	33	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	145	-	nC
Source-dra	in diode	•		ı		-
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; Fig. 14	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	47	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}; Fig. 15$	[1] -	48	-	nC

[1] includes capacitive recovery



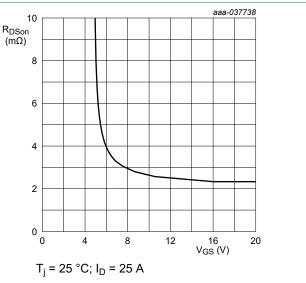


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

function of drain-source voltage; typical values

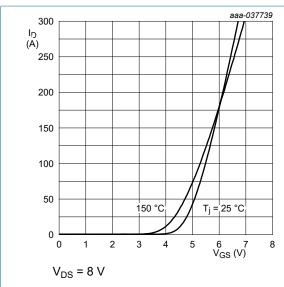


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

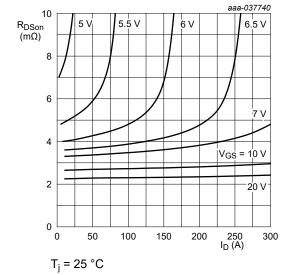


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

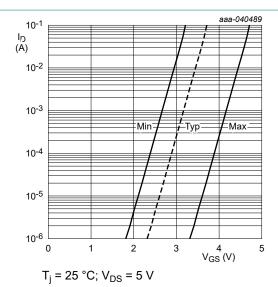


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

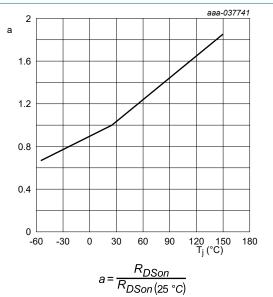


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

6/11

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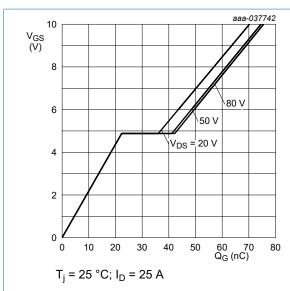


Fig. 11. Gate-source voltage as a function of gate charge; typical values

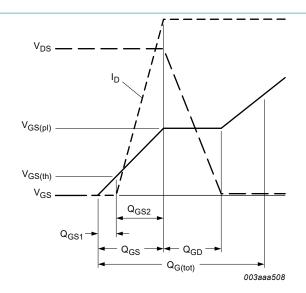


Fig. 12. Gate charge waveform definitions

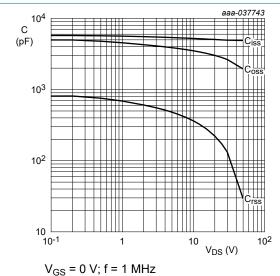
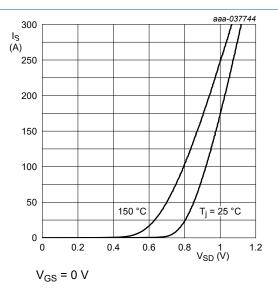


Fig. 13. Input, output and reverse transfer capacitances | Fig. 14. Source-drain (diode forward) current as a as a function of drain-source voltage; typical values



function of source-drain (diode forward) voltage; typical values

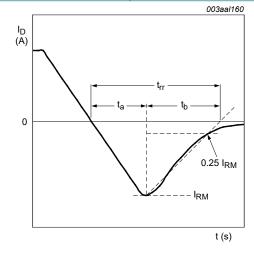


Fig. 15. Reverse recovery timing definition

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11. Package outline

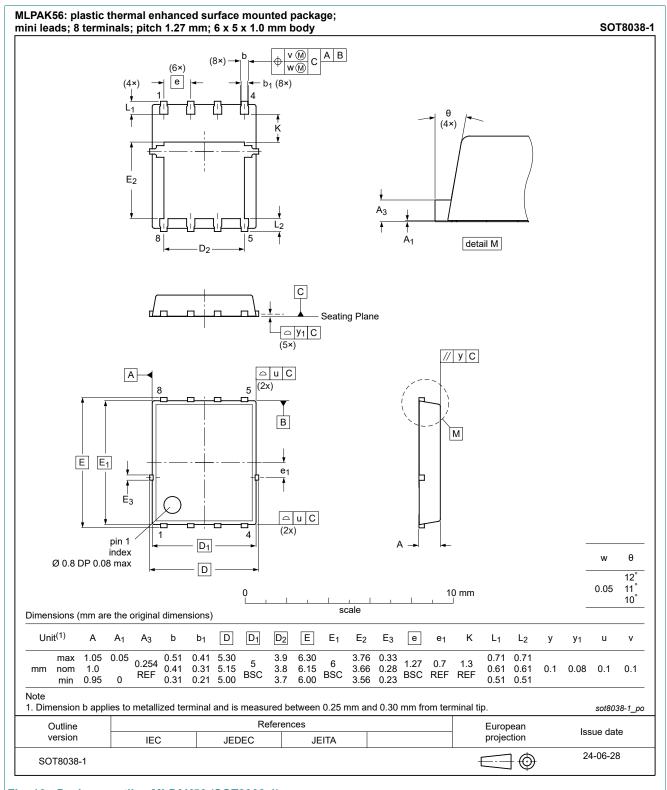
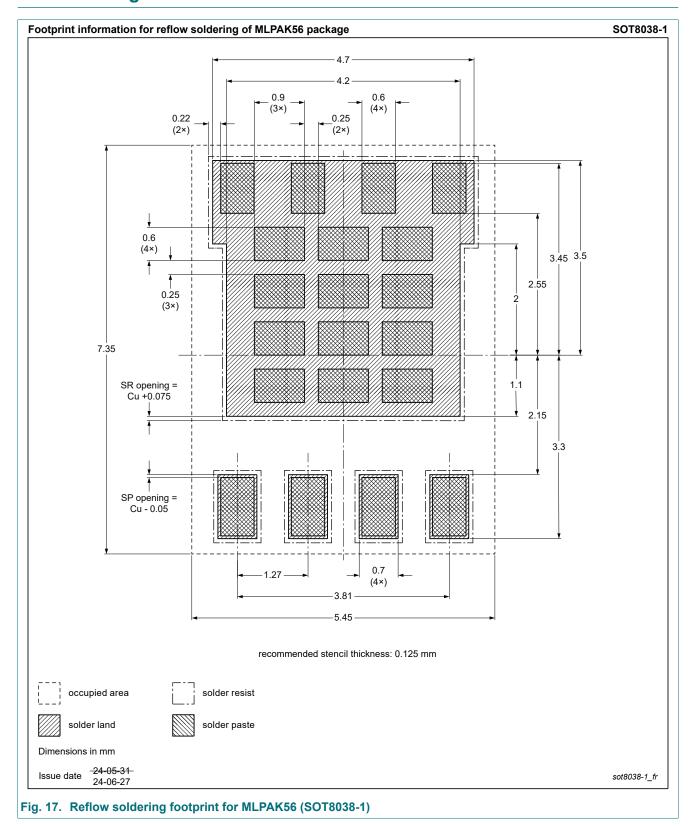


Fig. 16. Package outline MLPAK56 (SOT8038-1)

N-channel 100 V, 2.9 mOhm, standard level Trench MOSFET in MLPAK56

12. Soldering



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13. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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N-channel 100 V, 2.9 mOhm, standard level Trench MOSFET in MLPAK56

Contents

1.	General description	1
	Features and benefits	
	Applications	
	Quick reference data	
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
	Thermal characteristics	
10	. Characteristics	4
11.	. Package outline	8
	. Soldering	
	. Legal information	

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